

# High Voltage Power MOSFET

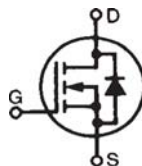
## IXTH1R4N250P3

$$V_{DSS} = 2500V$$

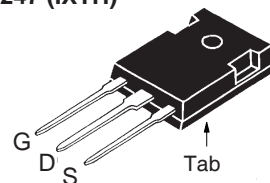
$$I_{D25} = 1.4A$$

$$R_{DS(on)} \leq 28\Omega$$

N-Channel Enhancement Mode  
Fast Intrinsic Diode



TO-247 (IXTH)



G = Gate      D = Drain  
S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	2500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	2500	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	1.4	A
$I_{D110}$	$T_C = 110^\circ\text{C}$	1.0	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	3.5	A
$P_D$	$T_C = 25^\circ\text{C}$	195	W
$T_J$		- 55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		- 55 ... +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
$M_d$	Mounting Torque	1.13/10	Nm/lb.in
<b>Weight</b>		6	g

### Features

- High Blocking Voltage
- Fast Intrinsic Diode
- Low Package Inductance

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- High Voltage Power Supplies
- Capacitor Discharge Applications
- Pulse Circuits
- Laser and X-Ray Generation Systems

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu\text{A}$	2500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu\text{A}$	2.0		4.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$ 250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.7A$ , Note 1			28 $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 60\text{V}$ , $I_D = 0.7\text{A}$ , Note 1	0.55	0.90	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		960	pF
$C_{oss}$			64	pF
$C_{rss}$			22	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 1250\text{V}$ , $I_D = I_{D25}$ $R_G = 5\Omega$ (External) Note 2		18	ns
$t_r$			24	ns
$t_{d(off)}$			39	ns
$t_f$			87	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 1250\text{V}$ , $I_D = 0.5 \cdot I_{D25}$		33.0	nC
$Q_{gs}$			4.0	nC
$Q_{gd}$			18.5	nC
$R_{thJC}$				0.64 $^\circ\text{C/W}$
$R_{thCS}$		0.21		$^\circ\text{C/W}$

### Source-Drain Diode

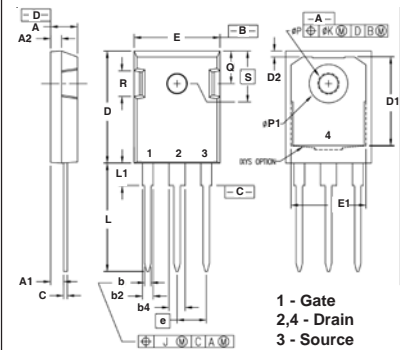
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			1.4 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			5.6 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = I_{D25}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ , $V_{GS} = 0\text{V}$		1.8	$\mu\text{s}$
$Q_{RM}$			16.7	$\mu\text{C}$
$I_{RM}$			18.8	A

- Notes:
1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .
  2. Additional provisions for lead-to-lead voltage isolation are required at  $V_{DS} > 1200\text{V}$ .

### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

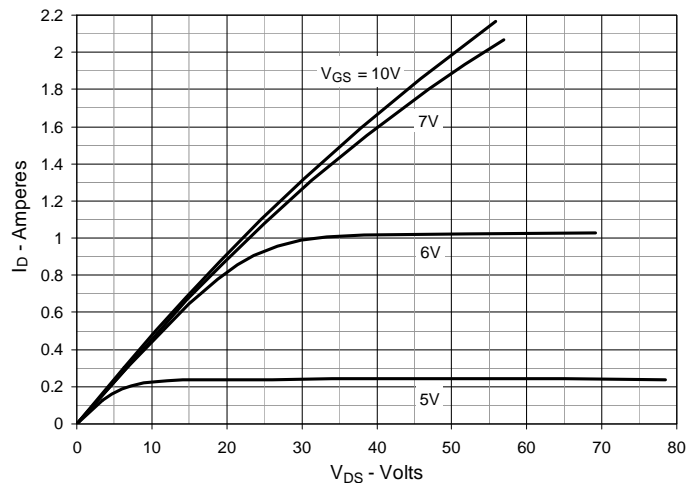
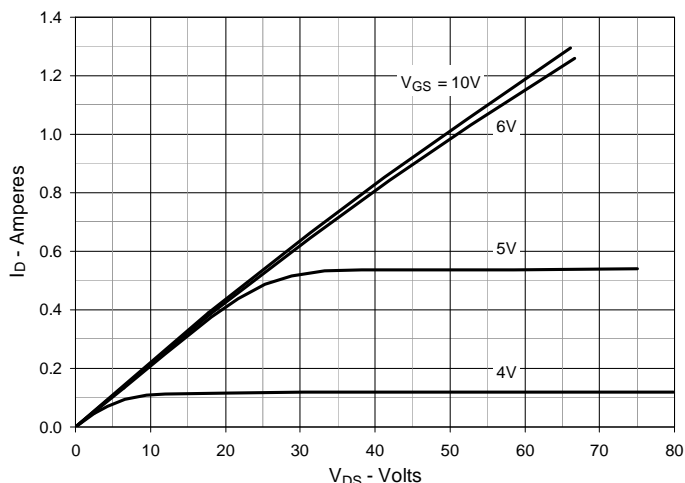
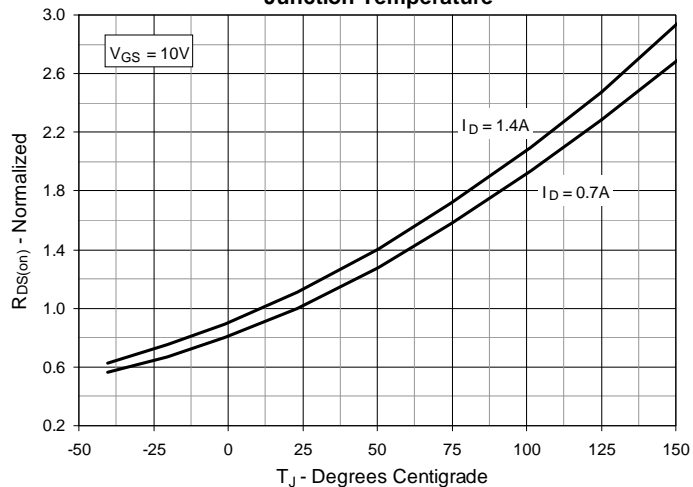
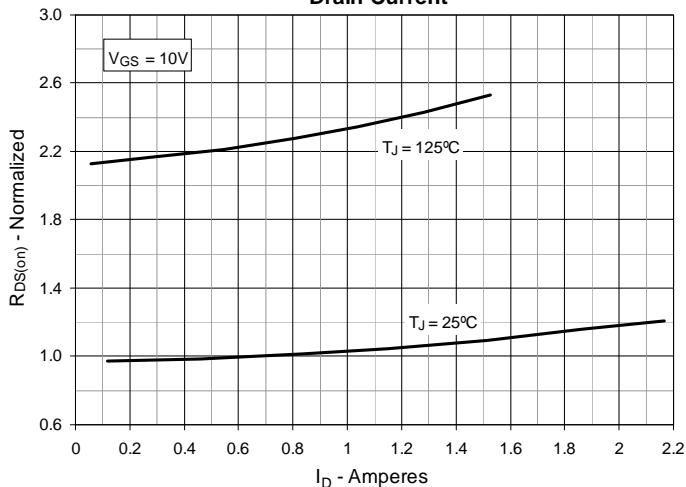
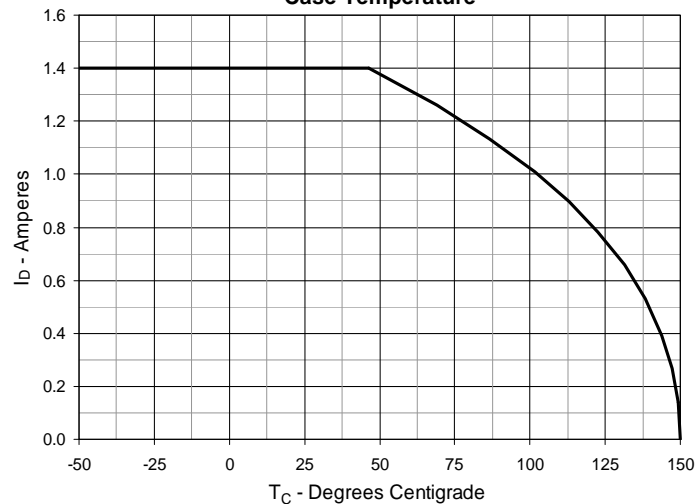
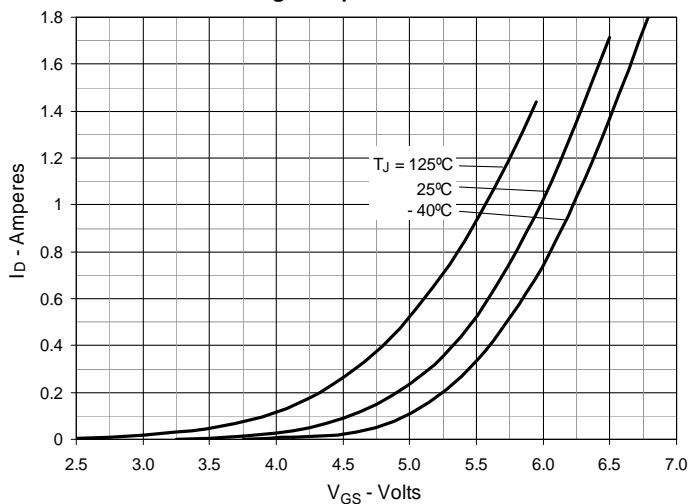
### TO-247 Outline

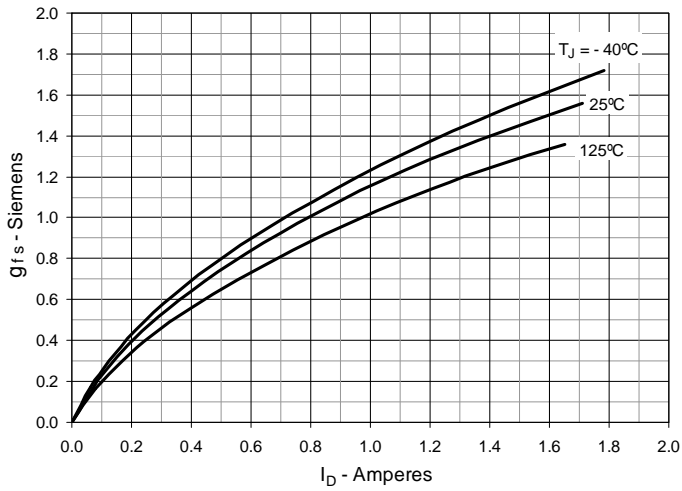
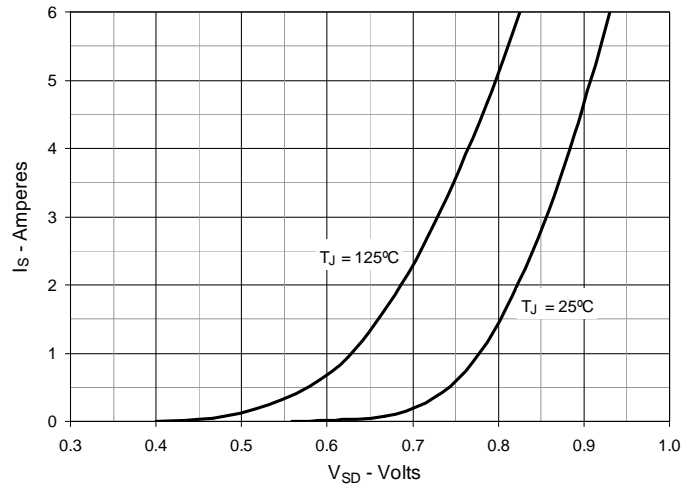
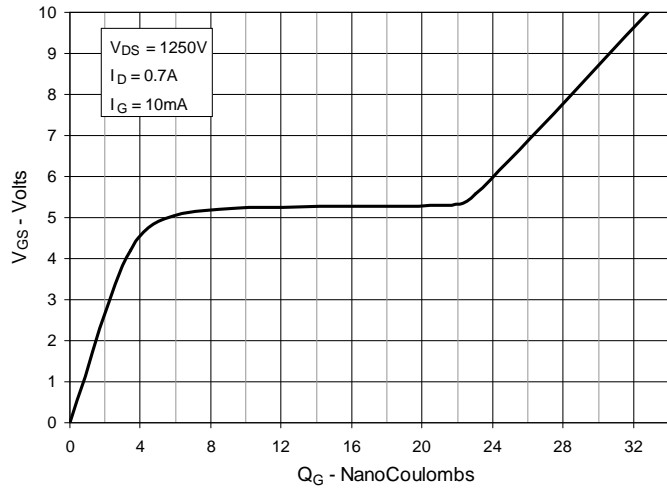
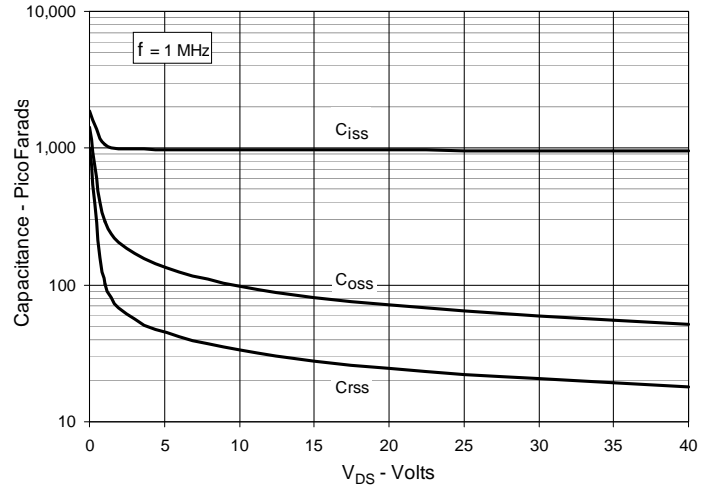
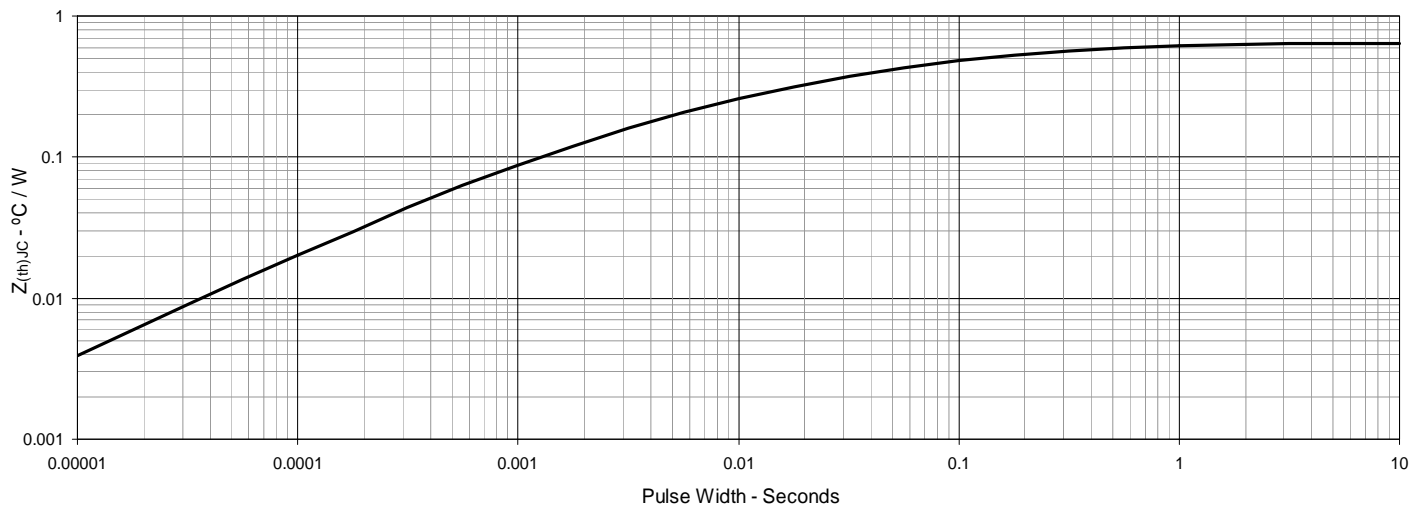


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Ø P1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	

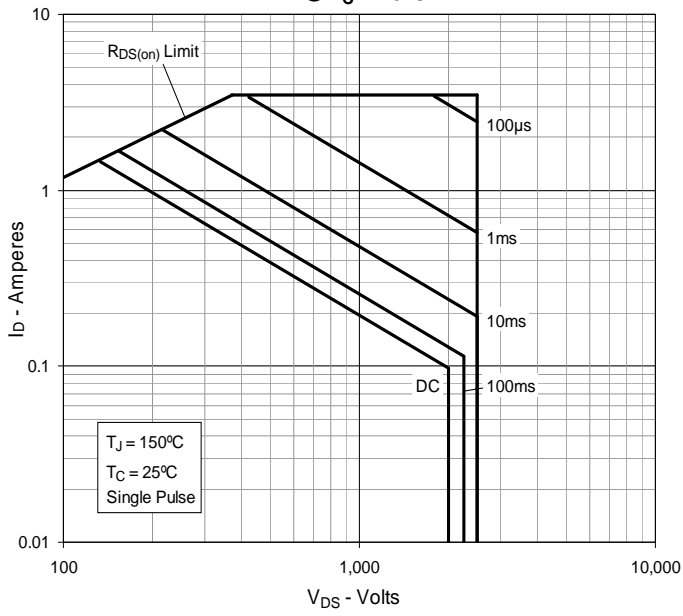
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

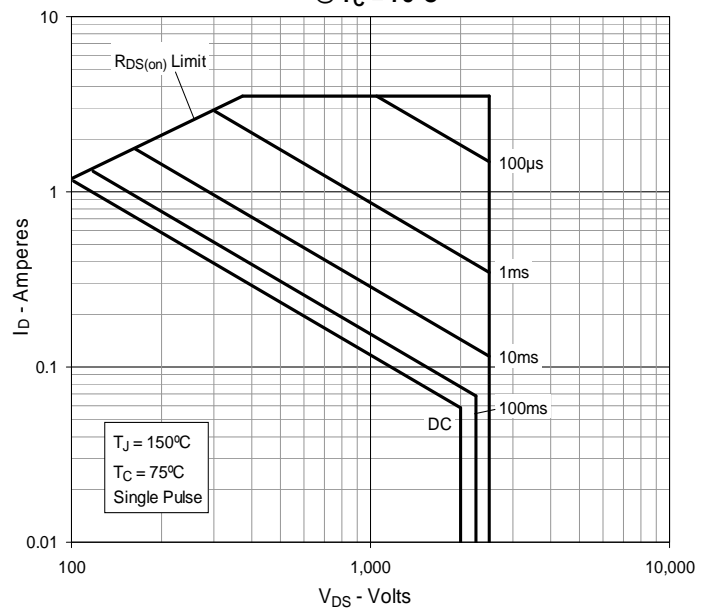
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 3.  $R_{DS(on)}$  Normalized to  $I_D = 0.7\text{A}$  Value vs. Junction Temperature**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 0.7\text{A}$  Value vs. Drain Current**

**Fig. 5. Maximum Drain Current vs. Case Temperature**

**Fig. 6. Input Admittance**


**Fig. 7. Transconductance**

**Fig. 8. Forward Voltage Drop of Intrinsic Diode**

**Fig. 9. Gate Charge**

**Fig. 10. Capacitance**

**Fig. 11. Maximum Transient Thermal Impedance**


**Fig. 12. Forward-Bias Safe Operating Area**  
@  $T_C = 25^\circ\text{C}$



**Fig. 13. Forward-Bias Safe Operating Area**  
@  $T_C = 75^\circ\text{C}$





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